

NSS20200LT1G, NSV20200LT1G

20 V, 4.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

Features

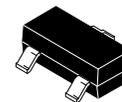
- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*



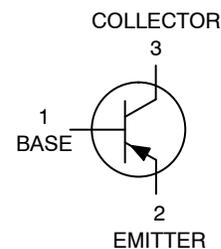
ON Semiconductor®

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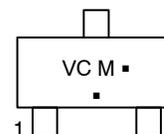
**-20 VOLTS
4.0 AMPS
PNP LOW $V_{CE(sat)}$ TRANSISTOR
EQUIVALENT $R_{DS(on)}$ 65 m Ω**



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



VC = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NSS20200LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSV20200LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-20	Vdc
Collector-Base Voltage	V _{CBO}	-20	Vdc
Emitter-Base Voltage	V _{EBO}	-7.0	Vdc
Collector Current - Continuous	I _C	-2.0	A
Collector Current - Peak	I _{CM}	-4.0	A
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 1)	460 3.7	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	270	°C/W
Total Device Dissipation T _A = 25°C Derate above 25°C	P _D (Note 2)	540 4.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	230	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P _{Dsingle} (Note 3)	710	mW
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-4 @ 100 mm², 1 oz. copper traces.
2. FR-4 @ 500 mm², 1 oz. copper traces.
3. Thermal response.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Breakdown Voltage ($I_C = -10\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-20	-	-	Vdc
Collector - Base Breakdown Voltage ($I_C = -0.1\text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	-20	-	-	Vdc
Emitter - Base Breakdown Voltage ($I_E = -0.1\text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	-7.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = -20\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-	-0.1	μAdc
Emitter Cutoff Current ($V_{EB} = -7.0\text{ Vdc}$)	I_{EBO}	-	-	-0.1	μAdc

ON CHARACTERISTICS

DC Current Gain (Note 4) ($I_C = -10\text{ mA}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -500\text{ mA}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -1.0\text{ A}$, $V_{CE} = -2.0\text{ V}$) ($I_C = -2.0\text{ A}$, $V_{CE} = -2.0\text{ V}$)	h_{FE}	250 250 180 150	- 300 - -	- - - -	
Collector - Emitter Saturation Voltage (Note 4) ($I_C = -0.1\text{ A}$, $I_B = -0.010\text{ A}$) (Note 5) ($I_C = -1.0\text{ A}$, $I_B = -0.100\text{ A}$) ($I_C = -1.0\text{ A}$, $I_B = -0.010\text{ A}$) ($I_C = -2.0\text{ A}$, $I_B = -0.200\text{ A}$)	$V_{CE(sat)}$	- - - -	-0.008 -0.065 -0.100 -0.130	-0.013 -0.090 -0.120 -0.180	V
Base - Emitter Saturation Voltage (Note 4) ($I_C = -1.0\text{ A}$, $I_B = -0.01\text{ A}$)	$V_{BE(sat)}$	-	-	-0.900	V
Base - Emitter Turn-on Voltage (Note 4) ($I_C = -1.0\text{ A}$, $V_{CE} = -2.0\text{ V}$)	$V_{BE(on)}$	-	-	-0.900	V
Cutoff Frequency ($I_C = -100\text{ mA}$, $V_{CE} = -5.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	-	-	MHz
Input Capacitance ($V_{EB} = 0.5\text{ V}$, $f = 1.0\text{ MHz}$)	C_{ibo}	-	-	330	pF
Output Capacitance ($V_{CB} = 3.0\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	-	-	100	pF

SWITCHING CHARACTERISTICS

Delay ($V_{CC} = -15\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_d	-	-	60	ns
Rise ($V_{CC} = -15\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_r	-	-	120	ns
Storage ($V_{CC} = -15\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_s	-	-	300	ns
Fall ($V_{CC} = -15\text{ V}$, $I_C = 750\text{ mA}$, $I_{B1} = 15\text{ mA}$)	t_f	-	-	130	ns

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle \leq 2%.

5. Guaranteed by design but not tested.

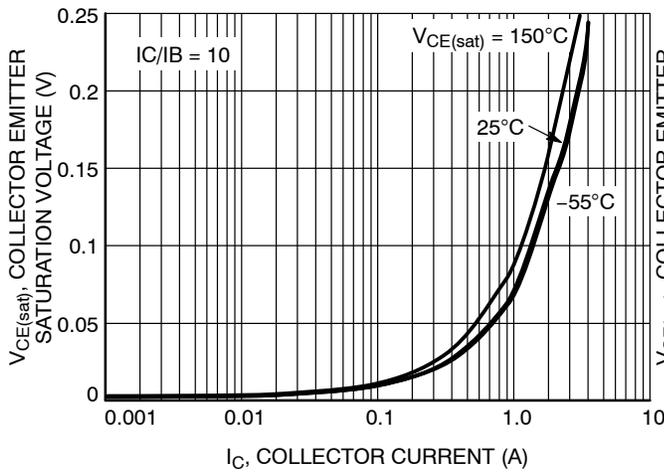


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

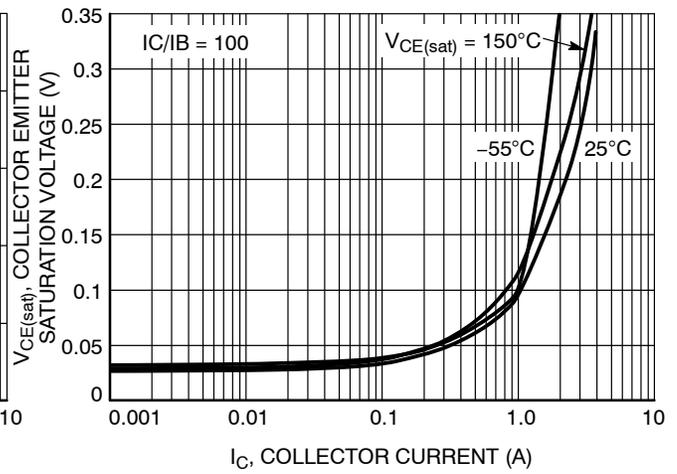


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

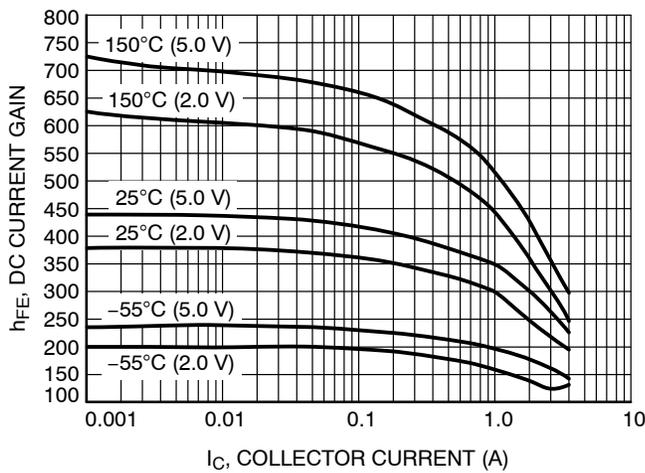


Figure 3. DC Current Gain vs. Collector Current

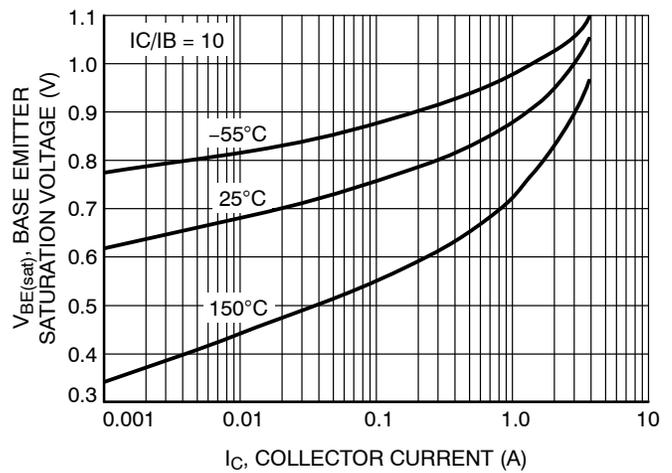


Figure 4. Base Emitter Saturation Voltage vs. Collector Current

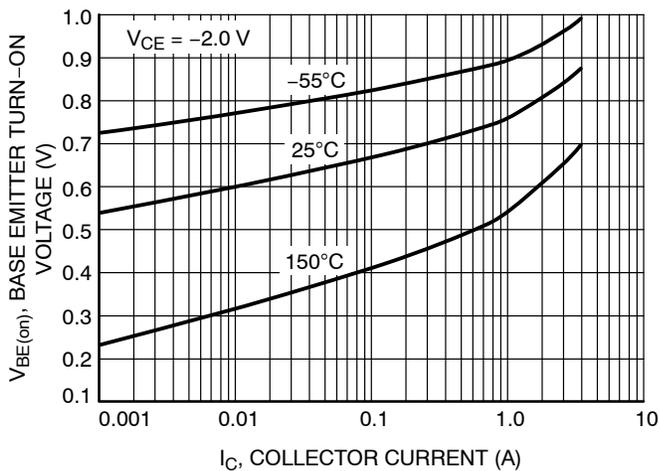


Figure 5. Base Emitter Turn-On Voltage vs. Collector Current

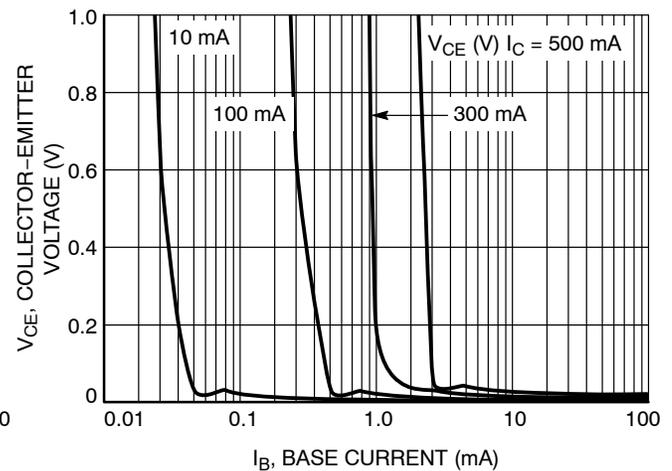


Figure 6. Saturation Region

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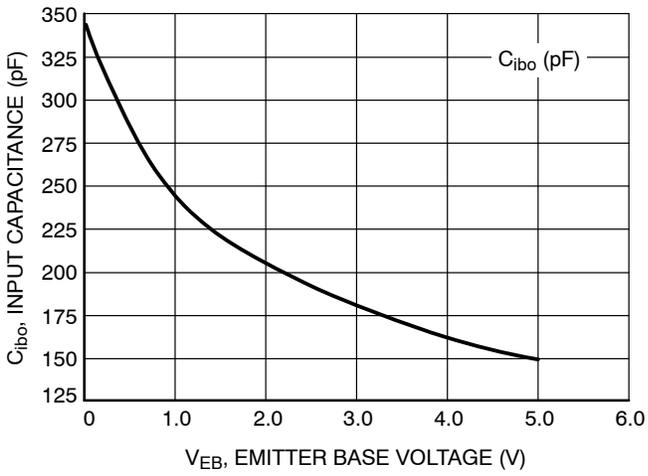


Figure 7. Input Capacitance

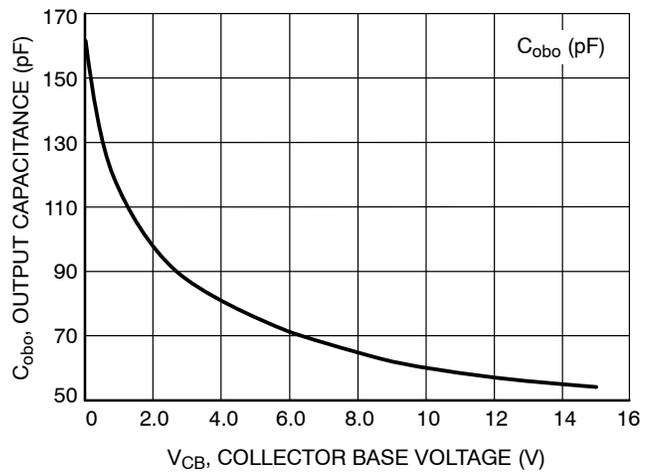


Figure 8. Output Capacitance

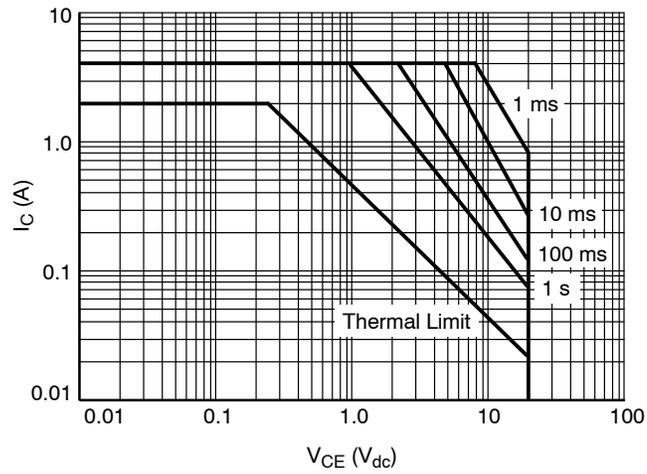
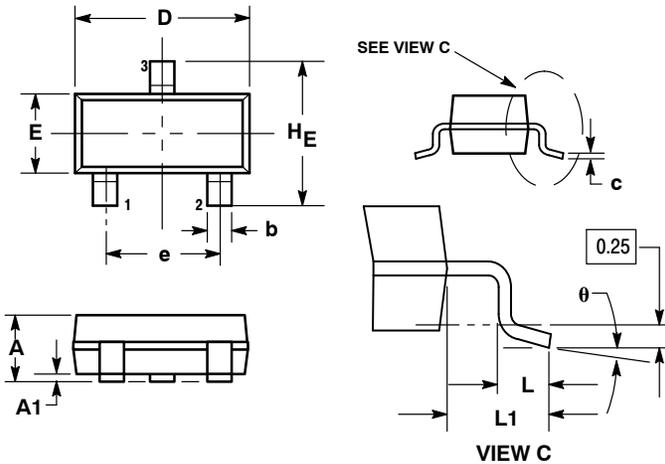


Figure 9. Safe Operating Area

NSS20200LT1G, NSV20200LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

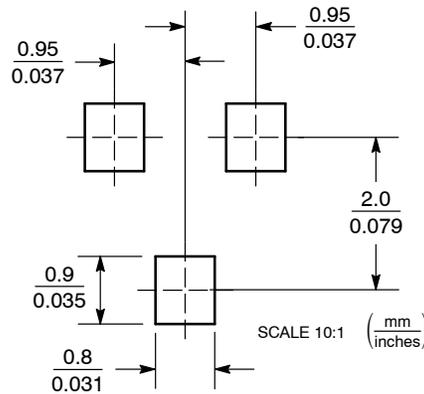
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT



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